



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SOT23 PNP SILICON PLANAR DARLINGTON TRANSISTORS

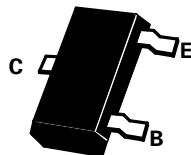
FMMTA63 FMMTA64

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PARTMARKING DETAIL – FMMTA63 - Z2U
FMMTA64 - Z2V

COMPLEMENTARY TYPES – FMMTA63 - FMMTA13
FMMTA64 - FMMTA14



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-10	V
Peak Pulse Current	I_{CM}	-800	mA
Continuous Collector Current	I_C	-500	mA
Peak Base Current	I_{BM}	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	FMMTA63		FMMTA64		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-30		-30		V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-30		-30		V	$I_C = -10mA, I_B = 0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-10		-10		V	$I_E = -10\mu A, I_C = 0$
Collector Cut-Off Current	I_{CBO}		-0.1		-0.1	μA	$V_{CB} = -30V, I_E = 0$
Emitter Cut-Off Current	I_{EBO}		-0.1		-0.1	μA	$V_{CE} = -10V$
Static Forward Current Transfer Ratio	h_{FE}	5K 10K		10K 20K			$I_C = -10mA, V_{CE} = 5V^*$ $I_C = -100mA, V_{CE} = 5V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-1.5		-1.5	V	$I_C = -100mA, I_B = -0.1mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-2.0		-2.0	V	$I_C = -100mA, I_B = -0.1mA^*$
Transition Frequency	f_T	125		125		MHz	$I_C = -50mA, V_{CE} = -5V$ $f = 20MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FZTA63 datasheet.